



Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f215rgt6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

·······							
Reference	Part numbers						
STM32F215xx	STM32F215RG, STM32F215VG, STM32F215ZG STM32F215RE, STM32F215VE, STM32F215ZE						
STM32F217xx	STM32F217VG, STM32F217IG, STM32F217ZG STM32F217VE, STM32F217IE, STM32F217ZE						

Table 1. Device summary



Contents

1	Introd	duction	13					
2	Desc	Description						
	2.1	Full compatibility throughout the family	17					
3	Func	Functional overview						
	3.1	ARM [®] Cortex [®] -M3 core with embedded Flash and SRAM	20					
	3.2	Adaptive real-time memory accelerator (ART Accelerator™)	20					
	3.3	Memory protection unit	20					
	3.4	Embedded Flash memory	21					
	3.5	CRC (cyclic redundancy check) calculation unit	21					
	3.6	Embedded SRAM	21					
	3.7	Multi-AHB bus matrix	21					
	3.8	DMA controller (DMA)	22					
	3.9	Flexible static memory controller (FSMC)	23					
	3.10	Nested vectored interrupt controller (NVIC)	23					
	3.11	External interrupt/event controller (EXTI)	24					
	3.12	Clocks and startup	24					
	3.13	Boot modes	24					
	3.14	Power supply schemes	25					
	3.15	Power supply supervisor	25					
	3.16	Voltage regulator	25					
		3.16.1 Regulator ON	25					
		3.16.2 Regulator OFF	26					
		3.16.3 Regulator ON/OFF and internal reset ON/OFF availability	28					
	3.17	Real-time clock (RTC), backup SRAM and backup registers	29					
	3.18	Low-power modes	29					
	3.19	V _{BAT} operation	30					
	3.20	Timers and watchdogs	30					
		3.20.1 Advanced-control timers (TIM1, TIM8)	31					
		3.20.2 General-purpose timers (TIMx)	32					
		3.20.3 Basic timers TIM6 and TIM7	32					



	ultra fine pitch ball grid array package outline	163
Figure 86.	UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball	
	grid array package recommended footprint	164
Figure 87.	UFBGA176+25 marking (package top view)	165



The DMA can be used with the main peripherals:

- SPI and I²S
- I²C
- USART and UART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDIO
- Cryptographic acceleration
- Camera interface (DCMI)
- ADC.

3.9 Flexible static memory controller (FSMC)

The FSMC is embedded in all STM32F21x devices. It has four Chip Select outputs supporting the following modes: PC Card/Compact Flash, SRAM, PSRAM, NOR Flash and NAND Flash.

Functionality overview:

- Write FIFO
- Code execution from external memory except for NAND Flash and PC Card
- Maximum frequency (f_{HCLK}) for external access is 60 MHz

LCD parallel interface

The FSMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

3.10 Nested vectored interrupt controller (NVIC)

The STM32F21x devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 81 maskable interrupt channels plus the 16 interrupt lines of the Cortex[®]-M3.

The NVIC main features are the following:

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead



Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary output	Max interface clock	Max timer clock
General	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	y integer tween 1 Yes 4 No 30 MHz	30 MHz	60 MHz		
purpose TIM3, TIM4 16-bit Up, Down, Up/down and	Any integer between 1 and 65536	Yes	4	No	30 MHz	60 MHz			
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	30 MHz	60 MHz
	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	o 60 MHz	120 MHz
General	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	60 MHz	120 MHz
purpose	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	30 MHz	60 MHz
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	30 MHz	60 MHz

Table 4. Timer feature comparison (continued)

3.20.1 Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The TIM1 and TIM8 counters can be frozen in debug mode. Many of the advanced-control timer features are shared with those of the standard TIMx timers which have the same architecture. The advanced-control timer can therefore work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.



		Pins	5							
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176	Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
22	31	42	52	P3	PA6	I/O	FT	(4)	SPI1_MISO, TIM8_BKIN, TIM13_CH1, DCMI_PIXCLK, TIM3_CH1, TIM1_BKIN, EVENTOUT	ADC12_IN6
23	32	43	53	R3	PA7	I/O	FT	(4)	SPI1_MOSI, TIM8_CH1N, TIM14_CH1, TIM3_CH2, ETH_MII_RX_DV, TIM1_CH1N, ETH_RMII_CRS_DV, EVENTOUT	ADC12_IN7
24	33	44	54	N5	PC4	I/O	FT	(4)	ETH_RMII_RXD0,/ ETH_MII_RXD0, EVENTOUT	ADC12_IN14
25	34	45	55	P5	PC5	I/O	FT	(4)	ETH_RMII_RXD1, ETH_MII_RXD1, EVENTOUT	ADC12_IN15
26	35	46	56	R5	PB0	I/O	FT	(4)	TIM3_CH3, TIM8_CH2N, OTG_HS_ULPI_D1, ETH_MII_RXD2, TIM1_CH2N, EVENTOUT	ADC12_IN8
27	36	47	57	R4	PB1	I/O	FT	(4)	TIM3_CH4, TIM8_CH3N, OTG_HS_ULPI_D2, ETH_MII_RXD3, TIM1_CH3N, EVENTOUT	ADC12_IN9
28	37	48	58	M6	PB2/BOOT1 (PB2)	I/O	FT	-	EVENTOUT	-
-	-	49	59	R6	PF11	I/O	FT	-	DCMI_D12, EVENTOUT	-
-	-	50	60	P6	PF12	I/O	FT	-	FSMC_A6, EVENTOUT	-
-	-	51	61	M8	V _{SS}	S	-	-	-	-
-	-	52	62	N8	V _{DD}	S	-	-	-	-
-	-	53	63	N6	PF13	I/O	FT	-	FSMC_A7, EVENTOUT	-
-	-	54	64	R7	PF14	I/O	FT	-	FSMC_A8, EVENTOUT	-
	-	55	65	P7	PF15	I/O	FT	-	FSMC_A9, EVENTOUT	-
-	-	56	66	N7	PG0	I/O	FT	-	FSMC_A10, EVENTOUT	-
	-	57	67	M7	PG1	I/O	FT	-	FSMC_A11, EVENTOUT	-
-	38	58	68	R8	PE7	I/O	FT	-	FSMC_D4, TIM1_ETR, EVENTOUT	-

Table 7. STM32F21x pin and ball definitions (continued)



6.1.6 Power supply scheme



Figure 17. Power supply scheme

 Each power supply pair must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

2. To connect REGOFF pin, refer to Section 3.16: Voltage regulator.

3. The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.

4. The 4.7 μF ceramic capacitor must be connected to one of the V_{DD} pin.

Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB, to ensure good device operation. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect device operation.



DocID17050 Rev 13

6.1.7 Current consumption measurement



Figure 18. Current consumption measurement scheme

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 10: Voltage characteristics*, *Table 11: Current characteristics*, and *Table 12: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Мах	Unit	
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} , V_{DD}) ⁽¹⁾	-0.3	4.0		
	Input voltage on five-volt tolerant pin ⁽²⁾	V _{SS} -0.3	V _{DD} +4	V	
V IN	Input voltage on any other pin	V _{SS} -0.3	4.0	l	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	m\/	
$ V_{SSX} - V_{SS} $	Variations between all the different ground pins	-	50	IIIV	
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3.14: Absolute maximum ratings (electrical sensitivity)		-	

Table 10.	Voltage	characteristics
-----------	---------	-----------------

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum value must always be respected. Refer to *Table 11* for the values of the maximum allowed injected current.



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
M	Brownout level 2	Falling edge	2.44	2.50	2.56	V
VBOR2	threshold	Rising edge	2.53	2.59	2.63	V
M	Brownout level 3	Falling edge	2.75	2.83	2.88	V
V _{BOR3}	threshold	Rising edge	2.85	2.92	2.97	V
V _{BORhyst} ⁽¹⁾	BOR hysteresis	-	-	100	-	mV
T _{RSTTEMPO} ⁽¹⁾⁽²⁾	Reset temporization	-	0.5	1.5	3.0	ms
I _{RUSH} ⁽¹⁾	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
E _{RUSH} ⁽¹⁾	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	V _{DD} = 1.8 V, T _A = 105 °C, I _{RUSH} = 171 mA for 31 μs	-	-	5.4	μC

Table 18. Embedded reset and	power control block characteristics	(continued)
		(

1. Guaranteed by design, not tested in production.

2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 18: Current consumption measurement scheme*.

All Run mode current consumption measurements given in this section are performed using ${\sf CoreMark}^{\textcircled{R}}$ code.



				Тур	Max ⁽¹⁾		
Symbol	ymbol Parameter	Conditions	^f нclĸ	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit
			120 MHz	38	51	61	
			90 MHz	30	43	53	
			60 MHz	20	33	43	
			30 MHz	11	25	35	
		External clock ⁽²⁾ , all peripherals enabled ⁽³⁾	25 MHz	8	21	31	
		F F	16 MHz	6	19	29	
			8 MHz	3.6	17.0	27.0	
			4 MHz	2.4	15.4	25.3	
	Supply current in		2 MHz	1.9	14.9	24.7	
'DD	Sleep mode		120 MHz	8	21	31	
			90 MHz	7	20	30	
			60 MHz	5	18	28	
			30 MHz	3.5	16.0	26.0	
		External clock ⁽²⁾ , all peripherals disabled	25 MHz	2.5	16.0	25.0	
			16 MHz	2.1	15.1	25.0	
			8 MHz	1.7	15.0	25.0	
			4 MHz	1.5	14.6	24.6	
			2 MHz	1.4	14.2	24.3	

Table 21. 1	Typical and	maximum	current	consum	ption in	Sleep	mode
-------------	-------------	---------	---------	--------	----------	-------	------

1. Guaranteed by characterization results, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.

2. External clock is 4 MHz and PLL is on when $\rm f_{HCLK}$ > 25 MHz.

3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).



6.3.8 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in *Table 27* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 13*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSE_ext}	External user clock source frequency ⁽¹⁾		1	-	26	MHz
V _{HSEH}	OSC_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V
V _{HSEL}	OSC_IN input pin low level voltage	-	V_{SS}	-	$0.3V_{\text{DD}}$	v
t _{w(HSE)} t _{w(HSE)}	OSC_IN high or low time ⁽¹⁾		5	-	-	ne
t _{r(HSE)} t _{f(HSE)}	OSC_IN rise or fall time ⁽¹⁾		-	-	20	115
C _{in(HSE)}	OSC_IN input capacitance ⁽¹⁾	-	-	5	-	pF
DuCy _(HSE)	Duty cycle	-	45	-	55	%
١	OSC_IN Input leakage current	V _{SS} ≤V _{IN} ≤V _{DD}	-	-	±1	μA

 Table 27. High-speed external user clock characteristics

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

The characteristics given in *Table 28* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 13*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSE_ext}	User External clock source frequency ⁽¹⁾		-	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage		$0.7 V_{\text{DD}}$	-	V_{DD}	V
V _{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{\text{DD}}$	v
t _{w(LSE)} t _{f(LSE)}	OSC32_IN high or low time ⁽¹⁾	-	450	-	-	ne
t _{r(LSE)} t _{f(LSE)}	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	115
C _{in(LSE)}	OSC32_IN input capacitance ⁽¹⁾	-	-	5	-	pF
DuCy _(LSE)	Duty cycle	-	30	-	70	%
ΙL	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA

|--|

1. Guaranteed by design, not tested in production.



The test results are given in *Table 40*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/ Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V _{DD} = 3.3 V, LQFP176, T _A = +25 °C, f _{HCLK} = 120 MHz, conforms to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V _{DD} = 3.3 V, LQFP176, T _A = +25 °C, f _{HCLK} = 120 MHz, conforms to IEC 61000-4-2	4A

	Table	40.	EMS	charac	teristics
--	-------	-----	-----	--------	-----------

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).







6.3.17 **NRST** pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see Table 48).

Unless otherwise specified, the parameters given in Table 48 are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in Table 13.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{PU}	Weak pull-up equivalent resistor ⁽¹⁾	$V_{IN} = V_{SS}$	30	40	50	kΩ
V _{F(NRST)} ⁽²⁾	NRST Input filtered pulse	-	-	-	100	ns
V _{NF(NRST)} ⁽²⁾	NRST Input not filtered pulse	V _{DD} > 2.7 V	300	-	-	ns
T _{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	_	μs

Table 48. NRST pin characteristics

The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series 1. resistance must be minimum (~10% order).

2. Guaranteed by design, not tested in production.



Figure 38. Recommended NRST pin protection

- The reset network protects the device against parasitic resets. 1.
- The user must ensure that the level on the NRST pin can go below the V_{IL(NRST)} max level specified in 2. Table 48. Otherwise the reset is not taken into account by the device.





Figure 40. SPI timing diagram - slave mode and CPHA = 0









Figure 45. USB OTG FS timings: definition of data signal rise and fall time

Table 57. USB OTG FS electrical characteristics⁽¹⁾

Driver characteristics							
Symbol	Parameter	Conditions	Min	Мах	Unit		
t _r	Rise time ⁽²⁾	C _L = 50 pF	4	20	ns		
t _f	Fall time ⁽²⁾	C _L = 50 pF	4	20	ns		
t _{rfm}	Rise/fall time matching	t _r /t _f	90	110	%		
V _{CRS}	Output signal crossover voltage	-	1.3	2.0	V		

1. Guaranteed by design, not tested in production.

2. Measured from 10% to 90% of the data signal. For more detailed informations, refer to USB Specification - Chapter 7 (version 2.0).

USB HS characteristics

Table 58 shows the USB HS operating voltage.

Table 58. USB HS DC electrical characteristics

Symbol		Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
Input level V _{DD} USB OTG HS operating voltage		2.7	3.6	V	

1. All the voltages are measured from the local ground potential.

Table 59. Clock timing parameters

Parameter ⁽¹⁾		Symbol	Min	Nominal	Max	Unit
Frequency (first transition)	8-bit ±10%	F _{START_8BIT}	54	60	66	MHz
Frequency (steady state) ±500	ppm	F _{STEADY}	59.97	60	60.03	MHz
Duty cycle (first transition) 8-bit ±10%		D _{START_8BIT}	40	50	60	%
Duty cycle (steady state) ±500	D _{STEADY}	49.975	50	50.025	%	
Time to reach the steady state frequency and duty cycle after the first transition		T _{STEADY}	-	-	1.4	ms
Clock startup time after the	Peripheral	T _{START_DEV}	-	-	5.6	me
de-assertion of SuspendM	Host	T _{START_HOST}	-	-	-	1115
PHY preparation time after the first transition of the input clock		T _{PREP}	-	-	-	μs

1. Guaranteed by design, not tested in production.



Symbol	Parameter	Min	Мах	Unit
t _{d(CLKL-} NADVL)	FSMC_CLK low to FSMC_NADV low	-	5	ns
t _{d(CLKL-} NADVH)	FSMC_CLK low to FSMC_NADV high	6	-	ns
t _{d(CLKL-AV)}	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	ns
t _{d(CLKL-AIV)}	FSMC_CLK low to FSMC_Ax invalid (x=1625)	8	-	ns
t _{d(CLKL-NWEL)}	FSMC_CLK low to FSMC_NWE low	-	1	ns
t _{d(CLKL-NWEH)}	FSMC_CLK low to FSMC_NWE high	1	-	ns
t _{d(CLKL-Data)}	FSMC_D[15:0] valid data after FSMC_CLK low	-	2	ns
t _{d(CLKL-NBLH)}	FSMC_CLK low to FSMC_NBL high	2	_	ns

Table 78. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾ (continued)

1. C_L = 30 pF.

2. Guaranteed by characterization results, not tested in production.

PC Card/CompactFlash controller waveforms and timings

Figure 63 through *Figure 68* represent synchronous waveforms, with *Table 79* and *Table 80* providing the corresponding timings. The results shown in these table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x04;
- COM.FSMC_WaitSetupTime = 0x07;
- COM.FSMC_HoldSetupTime = 0x04;
- COM.FSMC_HiZSetupTime = 0x00;
- ATT.FSMC_SetupTime = 0x04;
- ATT.FSMC_WaitSetupTime = 0x07;
- ATT.FSMC_HoldSetupTime = 0x04;
- ATT.FSMC_HiZSetupTime = 0x00;
- IO.FSMC_SetupTime = 0x04;
- IO.FSMC_WaitSetupTime = 0x07;
- IO.FSMC_HoldSetupTime = 0x04;
- IO.FSMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

In all timing tables, the T_{HCLK} is the HCLK clock period.





Figure 69. NAND controller waveforms for read access

Figure 70. NAND controller waveforms for write access







Symbol	Parameter	Conditions	Min	Мах	Unit		
f _{PP}	Clock frequency in data transfer mode	$C_L \le 30 \text{ pF}$	0	48	MHz		
-	SDIO_CK/f _{PCLK2} frequency ratio	-	-	8/3	-		
t _{W(CKL)}	Clock low time, f _{PP} = 16 MHz	$C_L \le 30 \text{ pF}$	32	-			
t _{W(CKH)}	Clock high time, f _{PP} = 16 MHz	$C_L \le 30 \text{ pF}$	31	-			
t _r	Clock rise time	$C_L \le 30 \text{ pF}$	-	3.5	ns		
t _f	Clock fall time	$C_L \le 30 \text{ pF}$	-	5			
CMD, D inputs (referenced to CK)							
t _{ISU}	Input setup time	$C_L \le 30 \text{ pF}$	2	-	200		
t _{IH}	Input hold time	$C_L \le 30 \text{ pF}$	0	-	115		
CMD, D outputs (referenced to CK) in MMC and SD HS mode							
t _{OV}	Output valid time	$C_L \le 30 \text{ pF}$	-	6	20		
t _{OH}	Output hold time	$C_L \le 30 \text{ pF}$	0.3	-	ns		
CMD, D outputs (referenced to CK) in SD default mode ⁽¹⁾							
t _{OVD}	Output valid default time	$C_L \le 30 \text{ pF}$	-	7	200		
t _{OHD}	Output hold default time	$C_L \le 30 \text{ pF}$	0.5	-	115		

Table 84. SD/MMC characteristics

1. Refer to SDIO_CLKCR, the SDI clock control register to control the CK output.

6.3.28 RTC characteristics

Table 85. RTC characteristics

Symbol	Parameter	Conditions	Min	Max
-	f _{PCLK1} /RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-





Figure 81. LQFP144 - 144-pin,20 x 20 mm low-profile quad flat package recommended footprint

1. Dimensions are expressed in millimeters.





Figure 84. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package recommended footprint

1. Dimensions are expressed in millimeters.

